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# XPX30P04A1

-30V P-Channe Enhancement Mode Power MOSFET

### Description

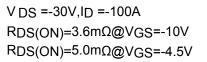
The XPX30P04A1 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

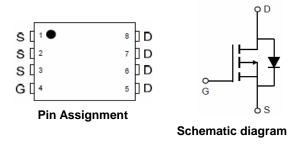
### **General Features**

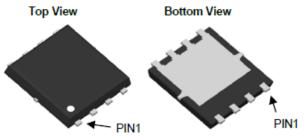
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

### Application

- Load switch
- Battery protection







## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX30P04A1	XPX30P04A1	DFN5X6-8L	-	-	5000

## Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	-100	А
Drain Current-Continuous(Tc=100℃)	I <sub>D</sub> (100℃)	-75	А
Pulsed Drain Current	I <sub>DM</sub>	-380	A
Maximum Power Dissipation	PD	72	W
Derating factor		0.7	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	455	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C
Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>ejc</sub>	2.1	°C/W



## Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-30		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-1.0	-1.5	-2.2	V
Drain Course On Chata Desistence		V <sub>GS</sub> =-10V, I <sub>D</sub> =-30A	-	3.6	4.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =-4.5V, I <sub>D</sub> =-20A	-	5.0	6.5	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =-5V,I <sub>D</sub> =-20A	-	30	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C <sub>lss</sub>		-	5189	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =-15V, $V_{GS}$ =0V,	-	688	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	592	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	17	-	nS
Turn-on Rise Time	tr	VDD=- 15V,ID=-30A	-	12	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	VGS=-10V,R G=1.6Ω	-	43	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg		-	62	-	nC
Gate-Source Charge	Q <sub>gs</sub>	VDS=-15V,ID=-30A, VGS=-10V	-	15		nC
Gate-Drain Charge	Q <sub>gd</sub>	VGG10V	-	19		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-30A	-	-	-1.5	V
Diode Forward Current (Note 2)	Is		-	-	-100	А
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =-20A	-		24	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	_		68	nC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t  $\leq$  10 sec.

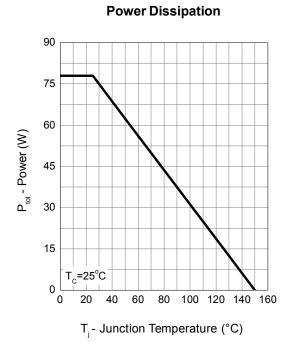
3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25  $^\circ C$  ,V\_DD=-20V,V\_G=-10V,L=0.5mH,Rg=25  $\Omega$ 



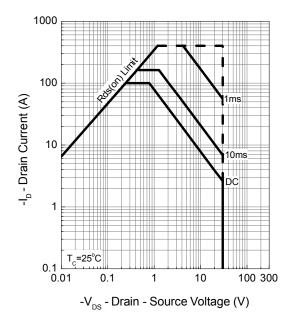
## **Typical Operating Characteristics**



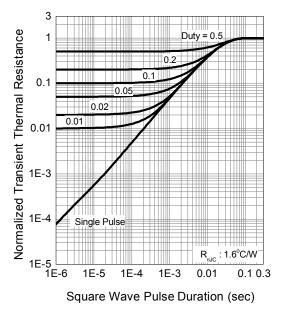
120 100 -I<sub>D</sub> - Drain Current (A) 80 60 40 20 T<sub>c</sub>=25°C,V<sub>g</sub>=10V 0 ้ด 80 60 100 120 140 160 20 40 T<sub>i</sub>- Junction Temperature (°C)

**Drain Current** 

Safe Operation Area

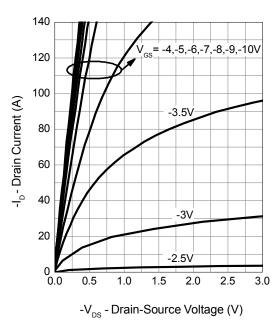


Thermal Transient Impedance



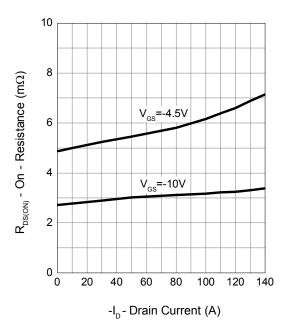


## **Typical Operating Characteristics (Cont.)**

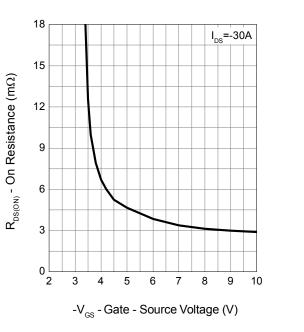


### **Output Characteristics**

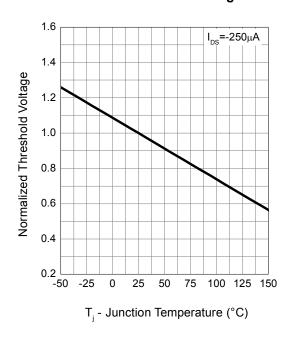
Drain-Source On Resistance



Gate Threshold Voltage



**Gate-Source On Resistance** 



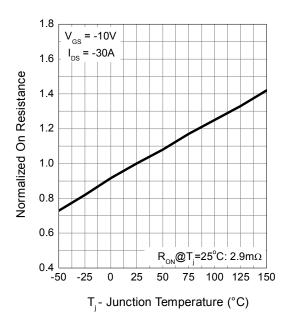


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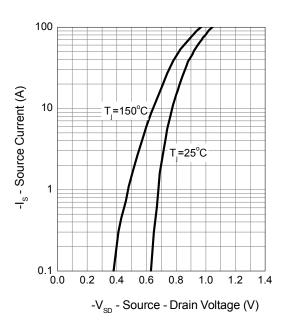
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## **Typical Operating Characteristics (Cont.)**

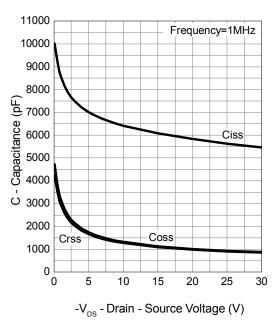


#### **Drain-Source On Resistance**

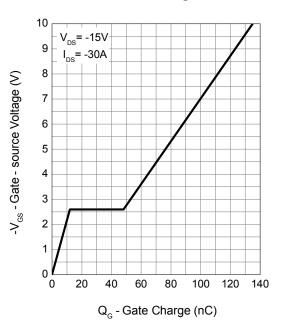
Source-Drain Diode Forward



#### Capacitance



Gate Charge

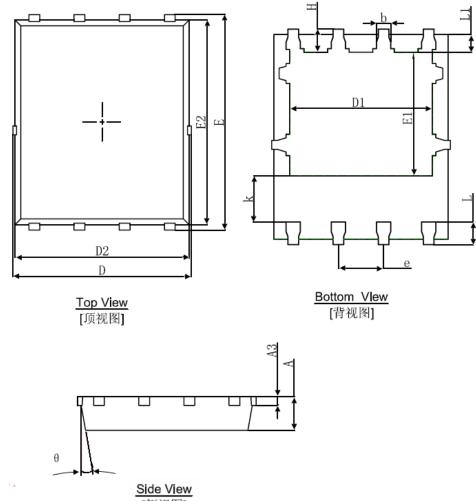




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## DFN5X6-8L Package Information



<u>[</u>侧视图]

Symphol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.900	1.000	0.035	0.039	
A3	0.254REF.		0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270TYP.		0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	



#### Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time	
Pb device	<b>245℃</b> ± <b>5</b> ℃	5sec±1sec	
Pb-Free device	<b>260</b> ℃+0/-5℃	5sec±1sec	



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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